

AOS Semiconductor Product Reliability Report

AO4813/AO4813L, rev B

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

495 Mercury Drive Sunnyvale, CA 94085 U.S.

Tel: (408) 830-9742

www.aosmd.com

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This AOS product reliability report summarizes the qualification result for AO4813. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4813 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation
- V. Quality Assurance Information

I. Product Description:

The AO4813 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and low gate charge. This device is suitable for use as a load switch or in PWM applications. Standard product AO4813 is Pb-free (meets ROHS & Sony 259 specifications). AO4813L is a Green Product ordering option. AO4813 and AO4813L are electrically identical.

Absolute Maximum Ratings T _A =25°C unless otherwise noted					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain T _A =25			-7.1		
Current	T _A =70°C	I _D	-5.6	А	
Pulsed Drain Current		I _{DM}	-30		
T _A =25°C		P _D	2	w	
Power Dissipation	T _A =70°C	I D	1.28	vv	
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

Thermal Characteristics							
Parameter	Symbol	Тур	Max	Units			
Maximum Junction-to- Ambient	T ≤ 10s	D	48	62.5	°C/W		
Maximum Junction-to- Ambient	Steady- State	- R _{θJA}	74	110	°C/W		
Maximum Junction-to-Lead	Steady- State	R _{θJL}	35	40	°C/W		



II. Die / Package Information:

Process Package Type Lead Frame Die Attach Bond wire Mold Material Filler % (Spherical/Flake) Flammability Rating Backside Metallization	AO4813 Standard sub-micron low voltage P channel process 8 leads SOIC Copper with Solder Plate Ag epoxy Au 2mils Epoxy resin with silica filler 90/10 UL-94 V-0 Ti / Ni / Ag	AO4813L (Green Compound) Standard sub-micron low voltage P channel process 8 leads SOIC Copper with Solder Plate Ag epoxy Au 2 mils Epoxy resin with silica filler 100/0 UL-94 V-0 Ti / Ni / Ag
Backside Metallization Moisture Level	Up to Level 1 *	Up to Level 1*

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4813 (Standard) & AO4813L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle IR reflow@260 °c Green: 168hr 85/85 THB+3 cycle IR reflow@260 °c	0hr	Standard: 81 lots Green: 23 lots	14410 pcs	0
HTGB	Temp = 150 °c , Vgs=100% of Vgsmax	168 / 500 hrs	4 lots	328 pcs	0
		1000 hrs	(Note A*)	77+5 pcs / lot	
HTRB	Temp = 150 °c , Vds=80% of Vdsmax	168 / 500 hrs	4 lots	328 pcs	0
		1000 hrs	(Note A*)	77+5 pcs / lot	
HAST	130 +/- 2 °c , 85%, 33.3 psi, Vgs = 80% of Vgs	100 hrs	Standard: 52 lots Green: 16 lots	3740 pcs	0
	max		(Note B**)	50+5 pcs / lot	
Pressure Pot	121 °c , 15+/-1 PSIG, RH=100%	96 hrs	Standard: 70 lots Green: 20 lots	4950 pcs	0
			(Note B**)	50+5 pcs / lot	
Temperature Cycle	-65 to 150 °c , air to air, 0.5hr per cycle	250 / 500 cycles	Standard: 81 lots Green: 23 lots	5720 pcs	0
-			(Note B**)	50+5 pcs / lot	



Continues					
DPA	Internal Vision	NA	5	5	0
	Cross-section		5	5	
	X-ray		5	5	
CSAM		NA	5	5	0
Bond Integrity	Room Temp	0hr	40	40 wires	0
	150°C bake	250hr	40	40 wires	
	150°C bake	500hr	40	40 wires	
Solderability	230 °c	5 sec	15	15 leads	0
Die shear	150 °c	0hr	10	10	0

III. Result of Reliability Stress for AO4813 (Standard) & AO4813L (Green)

Note A: The HTGB and HTRB reliability data presents total of available AO4813 and AO4813L burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO4813 and AO4813L comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 10.5

MTTF = 10872 years

500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4813). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 \text{ (N) (H) (Af)}] = 1.83 \times 10^9 / [2 (4 \times 164) (500) (258)] = 10.5$ MTTF = $10^9 / \text{FIT} = 9.52 \times 10^7 \text{hrs} = 10872 \text{years}$

Chi² = Chi Squared Distribution, determined by the nubr of failures and confidence interval \mathbf{N} = Total Number of units from HTRB and HTGB tests \mathbf{H} = Duration of HTRB/HTGB testing

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55° C) Acceleration Factor [**Af**] = **Exp** [Ea / **k** (1/Tj u - 1/Tj s)]

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Acceleration Factor ratio list:
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	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, 8.617164 X 10 $E^{-5}V/K$



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual. Guaranteed Outgoing Defect Rate: **< 25 ppm** Quality Sample Plan: conform to **Mil-Std-105D**